

Supplementary Information

Structural and optical properties of phosphorous doped nanocrystalline silicon deposited using VHF PECVD process for silicon heterojunction solar cells and optimization of simple p-n junction cell using SCAP-1D tool

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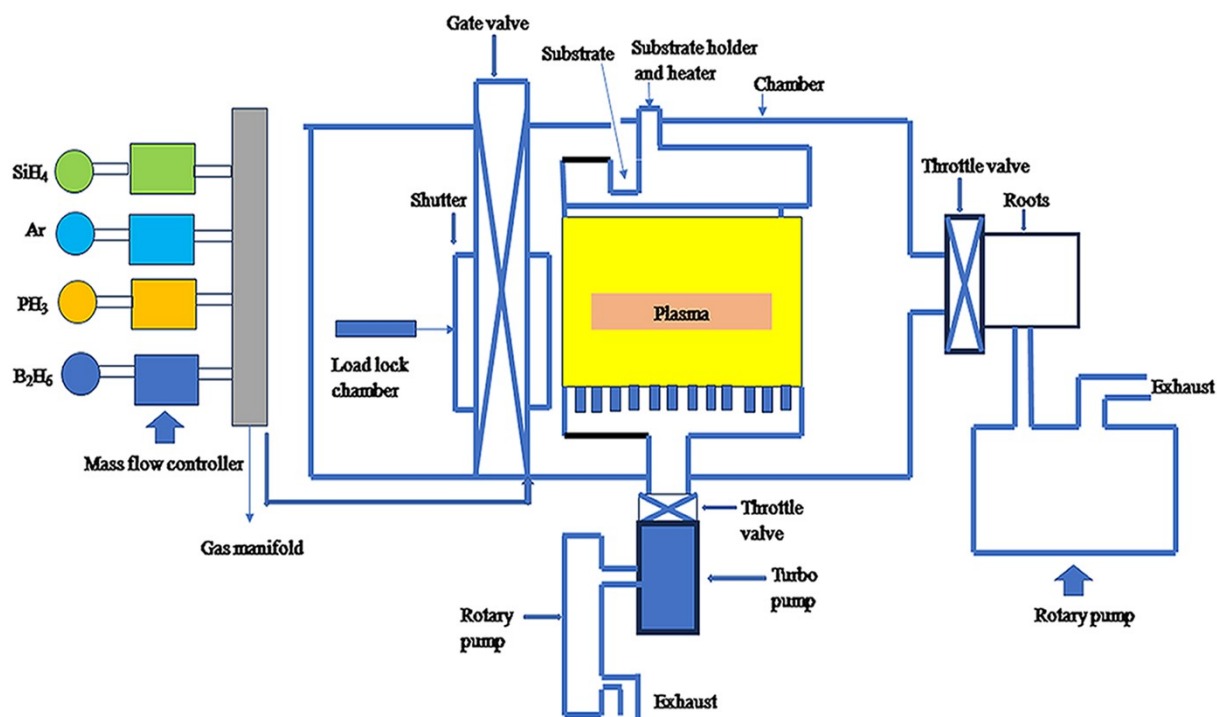


Figure S1. Schematic of PECVD system

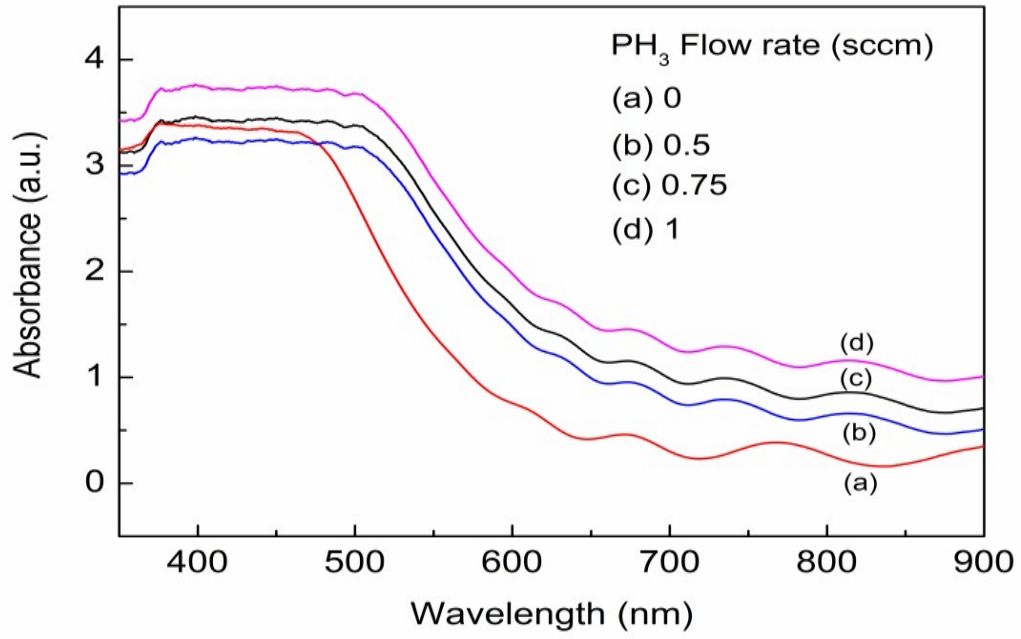


Figure S2. Absorption spectra of n type nc-Si:H films grown at different PH₃ flow rates (a) 0.0 (b) 0.5 (c) 0.75 and (d) 1 sccm